

| Ref # | Hits | Search Query  | DBs       | Default Operator | Plurals | Time Stamp       |
|-------|------|---|-----------|------------------|---------|------------------|
| L15   | 2    | bond adj pad and first adj mask and second adj mask and contiguous.clm.   | US-PGPU B | OR               | ON      | 2005/09/21 15:45 |
| L16   | 1    | (bond adj pad and first adj mask and second adj mask and contiguous).clm. | US-PGPU B | OR               | ON      | 2005/09/21 15:45 |

| Ref # | Hits  | Search Query  | DBs                              | Default Operator | Plurals | Time Stamp       |
|-------|-------|---|----------------------------------|------------------|---------|------------------|
| L1    | 8707  | (bond\$3 adj pad) with (trench via hole damascene groove aperture)  | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:14 |
| L2    | 11037 | (bond\$3 adj pad) with (trench via hole groove aperture damascene aperture opening recess)  | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:07 |
| L3    | 4687  | 2 and (dielectric insulat\$3) with (trench via hole groove aperture damascene aperture opening recess)  | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:07 |
| L4    | 1966  | 3 and (mask masking resist photoresist) with (trench via hole groove aperture damascene aperture opening recess)  | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:08 |
| L5    | 1966  | 4 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator)                    | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:09 |
| L6    | 1755  | 5 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with etch\$4       | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:10 |
| L7    | 951   | 6 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with ('cu' copper) | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR               | ON      | 2005/09/21 10:11 |

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| L8  | 608 | 7 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two)   | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:11 |
| L9  | 126 | 7 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region) | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:12 |
| L10 | 122 | 8 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region) | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:12 |
| L11 | 376 | 8 and (bond\$3 adj pad) with (method process)   | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:14 |
| L12 | 250 | 8 and (bond\$3 adj pad) near5 (method process)  | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>12:37 |
| L13 | 1   | 10/701423   | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>12:38 |
| L14 | 1   | 10/837528   | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>12:38 |
| S1  | 1   | 10/654240   | US-PGPU B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/13<br>17:33 |

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| S3  | 3     | "6362090"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/13<br>18:42 |
| S4  | 17839 | ((dielectric insulat\$3) with<br>(trench via hole damascene<br>groove aperture)) with<br>mask\$3 | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:05 |
| S5  | 9987  | S4 and (dielectric insulat\$3)<br>with (photoresist resist)                                      | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/13<br>18:45 |
| S6  | 201   | S5 and (dielectric insulat\$3)<br>with (bond\$3 adj pad)   | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/21<br>10:05 |
| S7  | 107   | S6 and ('cu' copper<br>interconnect\$3) with (bond\$3<br>adj pad)                                | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>06:51 |
| S8  | 3     | "6452271"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>06:52 |
| S9  | 4     | "6445069"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>06:55 |
| S10 | 6     | "6444489"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:00 |
| S11 | 1     | "6424090"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:01 |
| S12 | 17    | "6153940"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:04 |
| S13 | 17    | "6153940"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:05 |

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| S14 | 39    | "3986255"  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:05 |
| S15 | 16458 | ((bonding bond) near3 pad)<br>with (substrate dielectric<br>insulat\$3)                                  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:09 |
| S16 | 6774  | S15 and ((bonding bond)<br>near3 pad) with (trench hole<br>via groove aperture opening)                  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:10 |
| S17 | 343   | S16 and ((mask\$3 photoresist<br>resist) near3 pad) with<br>(trench hole via groove<br>aperture opening) | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>07:11 |
| S18 | 124   | S17 and ('cu' copper) with<br>(trench hole via groove<br>aperture opening)                               | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>08:34 |
| S19 | 1     | 10/964019  | US-PGPU<br>B;<br>USPAT;<br>EPO; JPO | OR | ON | 2005/09/14<br>08:34 |